

CLAIMS

[1] A method of orienting an electronic functional material, the method comprising:

a mixed material preparation step of preparing a mixed material from an electronic functional material and a matrix material used for orientating the electronic functional material;

an orientation step of orientating the mixed material; and

a matrix material removal step of removing the matrix material from the mixed material which has been oriented.

[2] The method of orienting an electronic functional material according to claim 1, wherein the electronic functional material contains an organic semiconductor compound.

[3] The method of orienting an electronic functional material according to claim 1, wherein the electronic functional material contains nanotubes.

[4] The method of orienting an electronic functional material according to claim 1, wherein the mixed material preparation step includes a mixed material layer formation step of forming a mixed material layer containing the mixed material.

[5] The method of orienting an electronic functional material according to claim 1, wherein, in the orientation step, the mixed material is oriented by at least any of drawing, shear deformation and liquid crystal orientation.

[6] The method of orienting an electronic functional material according to claim 1, wherein, in the matrix material removal step, the matrix material is removed by at least either heating or etching.

[7] The method of orienting an electronic functional material according to claim 1, wherein the matrix material contains a heat developable type resist material which is monomerized, sublimated and developed by heating after exposed to ultraviolet rays or irradiated with an electronic beam.

[8] The method of orienting an electronic functional material according to claim 1, wherein the matrix material contains a photosensitive polyphthalaldehyde base material.

[9] A method of fabricating an electronic functional material thin film by use of the electronic functional material orientation method of claim 1.

[10] A method of fabricating a thin-film transistor, wherein an electronic

functional material thin film that constitutes a semiconductor layer is formed by the electronic functional material thin film fabricating method of claim 9.

[11] An electronic functional material thin film produced by the electronic functional material thin film fabricating method of claim 9.

[12] A thin-film transistor having a semiconductor layer composed of the electronic functional material thin film of claim 11.